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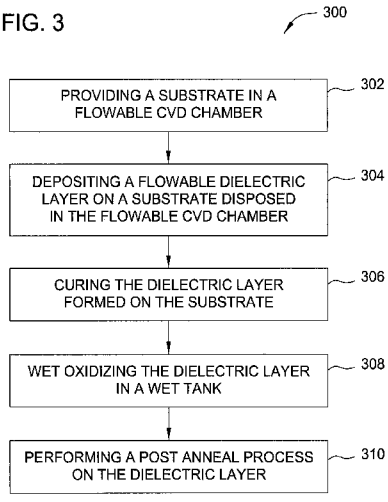
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(54) Title: WET OXIDATION PROCESS PERFORMED ON A DIELECTRIC MATERIAL FORMED FROM A FLOWABLE CVD PROCESS

FIG. 3



(57) Abstract: Methods of performing a wet oxidation process on a silicon containing dielectric material filling within trenches or vias defined within a substrate are provided. In one embodiment, a method of forming a dielectric material on a substrate includes forming a dielectric material on a substrate by a flowable CVD process, curing the dielectric material disposed on the substrate, performing a wet oxidation process on the dielectric material disposed on the substrate, and forming an oxidized dielectric material on the substrate.

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